

**BYW98-200**

HIGH EFFICIENCY FAST RECOVERY RECTIFIER DIODES

MAIN PRODUCT CHARACTERISTICS

I_{F(AV)}	3A
V_{RRM}	200 V
T_j (max)	150 °C
V_F (max)	0.85 V
t_{rr} (max)	35 ns

FEATURES AND BENEFITS

- VERY LOW CONDUCTION LOSSES
- NEGLIGIBLE SWITCHING LOSSES
- LOW FORWARD AND REVERSE RECOVERY TIMES

DESCRIPTION

Low voltage drop and rectifier suited for switching mode base drive and transistor circuits.



DO-201AD
(Plastic)

ABSOLUTE RATINGS (limiting values)

Symbol	Parameter		Value	Unit
V _{RRM}	Repetitive peak reverse voltage		200	V
I _{FRM}	Repetitive peak forward current *	t _p =5 μs F=1KHz	110	A
I _{F (AV)}	Average forward current*	T _a = 75°C δ = 0.5	3	A
I _{FSM}	Surge non repetitive forward current	t _p = 10ms Sinusoidal	70	A
T _{stg}	Storage temperature range		- 65 to + 150	°C
T _j	Maximum operating junction temperature		150	°C
T _L	Maximum lead temperature for soldering during 10s at 4mm from case		230	°C

* On infinite heatsink with 10mm lead length.

THERMAL RESISTANCE

Symbol	Parameter	Value	Unit
R _{th} (j-a)	Junction-ambient *	25	°C/W

* On infinite heatsink with 10mm lead length.

STATIC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Test Conditions		Min.	Typ.	Max.	Unit
I _R *	Reverse leakage current	T _j = 25°C	V _R = V _{RRM}			10	μA
		T _j = 100°C				0.5	mA
V _F **	Forward voltage drop	T _j = 25°C	I _F = 9A			1.2	V
		T _j = 100°C	I _F = 3A		0.78	0.85	

Pulse test : * t_p = 5 ms, δ < 2 %

** t_p = 380 μs, δ < 2 %

To evaluate the conduction losses use the following equations:

$$P = 0.75 \times I_F(AV) + 0.04 I_F^2(RMS)$$

RECOVERY CHARACTERISTICS

Symbol	Test Conditions			Min.	Typ.	Max.	Unit
t _{rr}	T _j = 25°C V _R = 30V	I _F = 1A	dI _F /dt = - 50A/μs			35	ns
Q _{rr}	T _j = 25°C V _R ≤ 30V	I _F = 3A	dI _F /dt = - 20A/μs		15		nC
t _{fr}	T _j = 25°C Measured at 1.1 x V _F max	I _F = 3A	dI _F /dt = - 50A/μs		20		ns
V _{FP}	T _j = 25°C	I _F = 3A	dI _F /dt = - 50A/μs		5		V

Fig. 1: Average forward power dissipation versus average forward current.

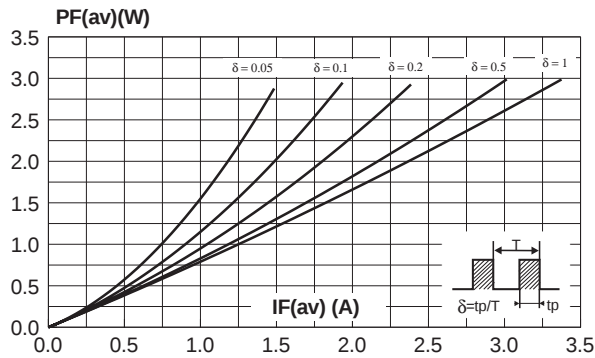


Fig. 2: Average forward current versus ambient temperature ($\delta=0.5$).

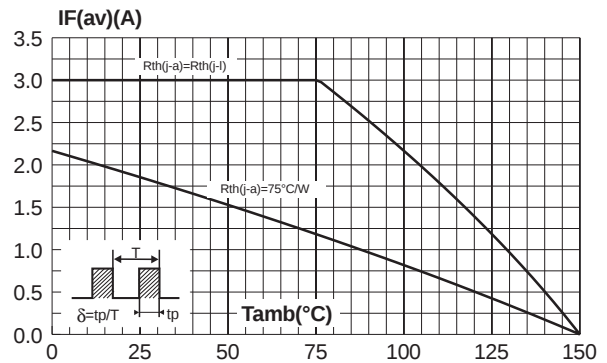


Fig. 3: Thermal resistance versus lead length.

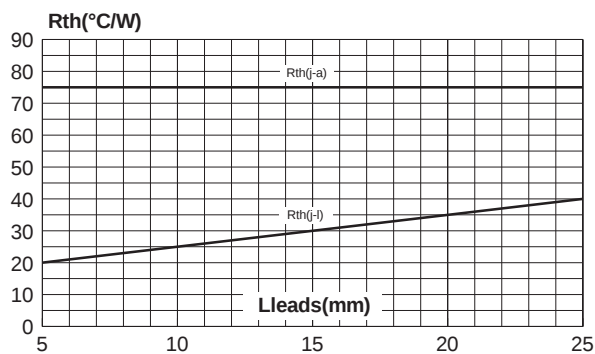


Fig. 4: Variation of thermal impedance junction to ambient versus pulse duration (recommended pad layout, epoxy FR4, $e(Cu)=35\mu m$).

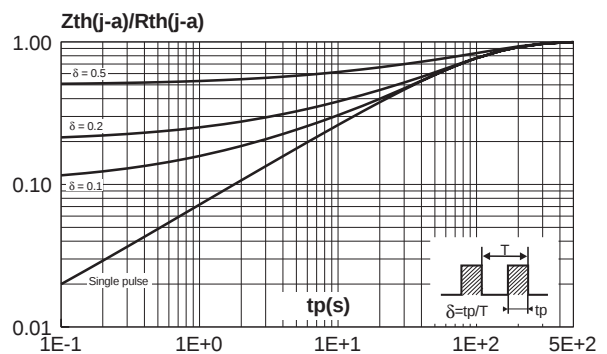


Fig. 5: Forward voltage drop versus forward current (maximum values).

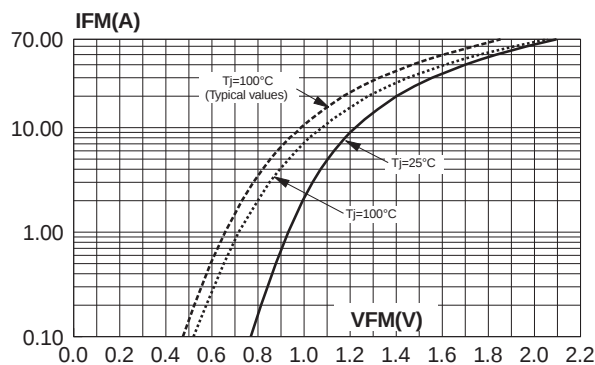


Fig. 6: Junction capacitance versus reverse voltage applied (typical values).

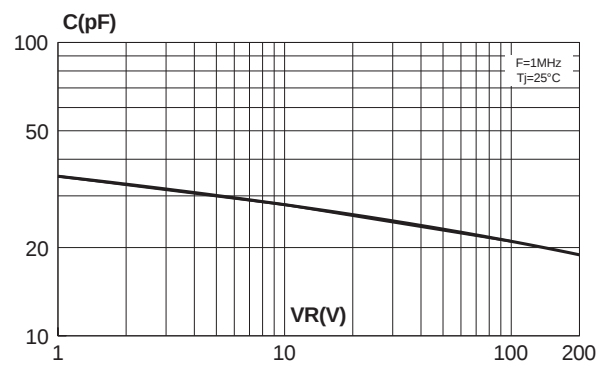


Fig. 7: Reverse recovery time versus di_F/dt .

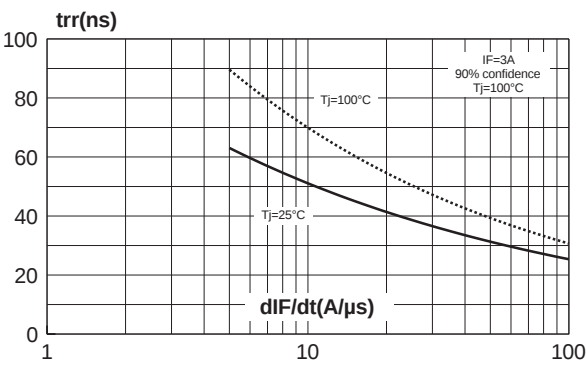


Fig. 8: Peak reverse recovery current versus di_F/dt .

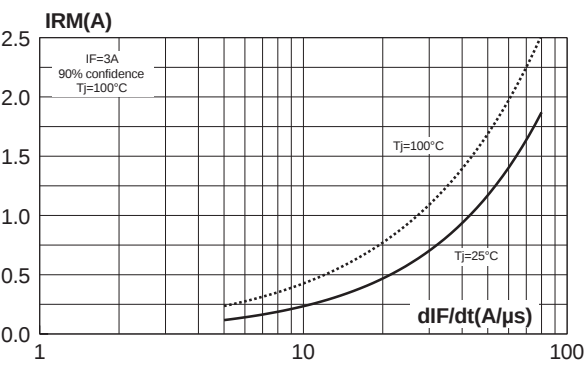
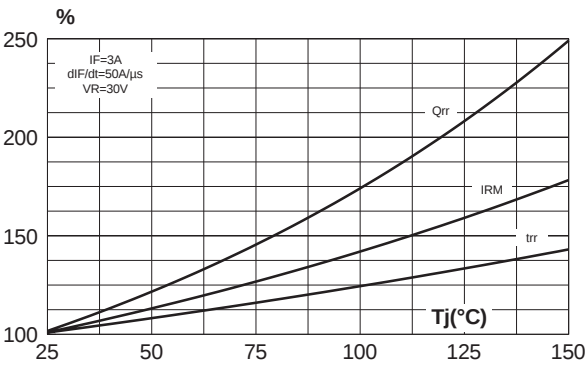
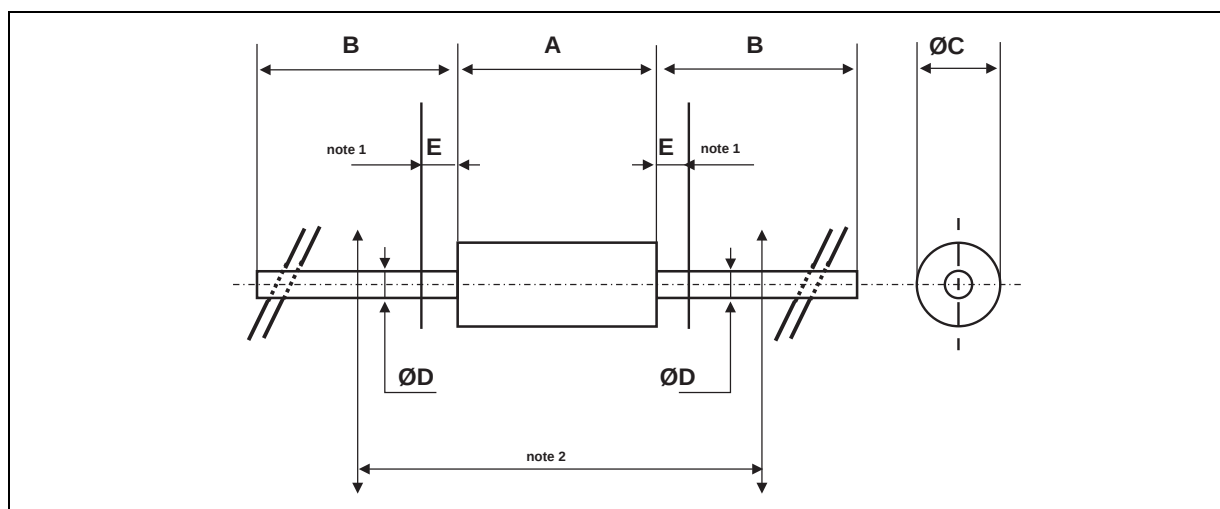


Fig. 9: Dynamic parameters versus junction temperature.



PACKAGE MECHANICAL DATA

DO-201AD



REF.	DIMENSIONS				NOTES
	Millimeters		Inches		
	Min.	Max.	Min.	Max.	
A		9.50		0.374	1 - The lead diameter Ø D is not controlled over zone E 2 - The minimum axial length within which the device may be placed with its leads bent at right angles is 0.59"(15 mm)
B	25.40		1.000		
Ø C		5.30		0.209	
Ø D		1.30		0.051	
E		1.25		0.049	

Ordering code	Marking	Package	Weight	Base qty	Delivery mode
BYW98-200	BYW98-200	DO-201AD	1.16 g.	600	Box
BYW98-200RL	BYW98-200	DO-201AD	1.16 g.	1900	Tape and reel

- White band indicates cathode
- Epoxy meets UL94,V0

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